1 Chapter 1

• Energy E of a photon of light in eV:

$$\lambda = \frac{1.24eV}{E}$$

• Distance D between adjacent planes in cubic lattices:

$$D = \frac{a}{\sqrt{h^2 + k^2 + l^2}}$$

• Angle between 2 Miller index directions A and B:

$$\cos(\theta) = \frac{A \bullet B}{|A||B|}$$

2 Chapter 2

• Planck relationship:

$$E = hv = (\frac{h}{2\pi})(2\pi v) = \hbar\omega$$

• Classical energy of a particle:

$$\frac{1}{2}mv^2 = \frac{1}{2}\frac{m^2v^2}{m} = \frac{\rho^2}{2m}$$

• De Broglie:

$$\lambda = \frac{h}{\rho} = \frac{h}{mv} \Rightarrow \rho = \frac{h}{\lambda} = \frac{h}{2\pi} \frac{2\pi}{\lambda} = \hbar k$$

• Momentum or energy in terms of k can be derived by combining De Broglie with the classical energy of a particle:

$$E = \hbar\omega = \frac{\rho^2}{2m} = \frac{\hbar^2 k^2}{2m}$$

• Rydberg Constant:

$$R = 109,678cm^{-1}$$

• Lyman:

$$v = cR(\frac{1}{1^2} - \frac{1}{n^2}), n = 2, 3, 4, \dots$$

• Balmer:

$$v = cR(\frac{1}{2^2} - \frac{1}{n^2}), n = 3, 4, 5...$$

• Paschen:

$$v = cR(\frac{1}{3^2} - \frac{1}{n^2}), n = 4, 5, 6, \dots$$

• Postulate for Bohr:

$$\rho_0 = n\hbar, n = 1, 2, 3, 4, \dots$$

• Finding radial forces on orbiting electron: (Electrical force toward nucleus) = (Equivalent force in terms of radial acceleration)

$$-\frac{q^2}{kr^2} = -\frac{mv^2}{r}$$

$$\rho_0 = n\hbar = mvr \Rightarrow mv^2 = \frac{m^2v^2}{m} = \frac{n^2\hbar^2}{mr^2}$$

$$\frac{q^2}{kr^2} = \frac{1}{mr}\frac{n^2\hbar^2}{r^2} \Rightarrow r_n = \frac{kn^2\hbar^2}{mq^2}$$

 $|r_n|$ is the radius of the nth orbit

$$-\frac{q^2}{kr^2} = -\frac{mv^2}{r} \Rightarrow \frac{n\hbar}{rm} \Rightarrow = \frac{q^2}{kn\hbar}$$

by subbing r from above.

$$\Rightarrow$$
 K.E. of $e^- =$

$$\frac{1}{2}mv^2 = \frac{mq^4}{2k^2n^2\hbar^2}$$

P.E. of
$$e^- =$$

$$-\frac{q^2}{kr_n} = -\frac{mq^4}{k^2n^2\hbar^2}$$

by subbing r

Total Energy of $e^- =$

$$E_n = KE = PE = -\frac{mq^4}{2k^2n^2\hbar^2} = -KE$$

• Energy difference between orbits:

$$E_{n2}-E_{n1}=\frac{mq^4}{2k^2\hbar^2}(\frac{1}{n_1^2}-\frac{1}{n_2^2})$$

• Frequency of light given by a transition between orbits:

$$V_{21} = \left[\frac{mq^4}{2k^2\hbar^2h}\right] \left(\frac{1}{n_1^2} - \frac{1}{n_2^2}\right)$$

• Heisenberg uncertainty principle:

$$(\Delta x)(\Delta \rho_x) \ge \frac{\hbar}{2} \tag{1}$$

$$(\Delta E)(\Delta t) \ge \frac{\hbar}{2} \tag{2}$$

2.1 Quantum Mechanics

Classical Variable	\rightarrow	Quantum Operator
x	\longrightarrow	x
f(x)	\longrightarrow	f(x)
$\rho(x)$	\longrightarrow	$\frac{\hbar}{i} \frac{\partial}{\partial x}$
E	\longrightarrow	$-\frac{\hbar}{i}\frac{\partial}{\partial t}$

• Normalization of the probability density (the wave function is the probability density):

$$\int_{-\infty}^{\infty} \Psi^* \Psi dx dy dz = 1 \tag{3}$$

• Time averaged expectation of the particle state

$$\langle Q \rangle = \int_{-\infty}^{\infty} \Psi^* Q_{op} \Psi dx dy dz$$
 (4)

• Classical energy of a partical:

$$KE + PE = E \Rightarrow \frac{1}{2}mv^2 + V = E \tag{5}$$

$$\frac{1}{2}mv^{2} = \frac{1}{2}\frac{(mv)^{2}}{m} = \frac{1}{2}\frac{\rho^{2}}{m} = \frac{\rho^{2}}{2m} \Rightarrow \frac{\rho^{2}}{2m} + V = E$$

$$\rho \to \frac{\hbar}{j}\frac{\partial}{\partial x}, E \to -\frac{\hbar}{j}\frac{\partial}{\partial t}$$

$$\Rightarrow \frac{-1}{2m}\hbar\frac{\partial^{2}}{\partial x^{2}}\Psi(x,t) + V(x)\Psi(x,t) = \frac{-\hbar}{j}\frac{\partial\Psi(x,t)}{\partial t}$$
(6)

where

$$(\frac{\partial}{\partial x})^2 \to \frac{\partial^2}{\partial x^2}, j^2 = -1$$

• Wave function in 3D then:

$$\frac{-\hbar}{2m}\nabla^2\Psi + V\Psi = \frac{-\hbar}{j}\frac{\partial\Psi}{\partial t} \ni \nabla^2\Psi = \frac{\partial^2\Psi}{\partial x^2} + \frac{\partial^2\Psi}{\partial y^2} + \frac{\partial^2\Psi}{\partial z^2}$$
 (7)

• Separation of variables:

$$\frac{-\hbar}{2m}\frac{\partial^2 \Psi(x,t)}{\partial x^2} + V(x)\Psi(x,t) = \frac{-\hbar}{j}\frac{\partial \Psi(x,t)}{\partial t}$$
(8)

 \Rightarrow

$$-\frac{\hbar}{2m}\frac{\partial^2 \psi(x)}{\partial x^2}\phi(t) + V(x)\psi(x)\phi(t) = -\frac{\hbar}{j}\psi(x)\frac{\partial\phi}{\partial t}$$
(9)

 $\frac{d\phi(t)}{dt} + \frac{j}{\hbar}E\phi(t) = 0 \tag{10}$

(time dependent portion)

$$-\frac{\hbar}{2m}\frac{d^2\psi(x)}{dx^2} + V(x)\psi(x) = E\psi(x) \tag{11}$$

(time independent portion)

- \bullet E \equiv equivalent constant, corresponds to total energy of the particle
- Wave function as linear combination of various eigenfunctions

$$\psi(x,t) = \sum_{n} C_n \Psi_n e^{-j\frac{E_n}{\hbar t}} \ni E_n \equiv nth \ prefactor$$
 (12)

• Infinite potential well

$$V(x) = \begin{cases} 0, & x \neq 0 \text{ and } x \neq L \\ \infty, & x = 0 \text{ or } x = L \end{cases}$$

$$\left(\frac{\hbar^2}{2m}\frac{d^2}{dx^2} + V(x)\right)\psi(x) = E\psi(x) \Rightarrow \frac{d^2\psi(x)}{dx^2} = \frac{2m}{\hbar}E\psi(x)$$
(13)

 \Rightarrow

$$\frac{d^2\psi(x)}{dx^2} + \frac{2m}{\hbar^2}E\psi(x) = 0$$

$$\Rightarrow \tag{14}$$

$$\psi(x) = \{\sin(kx), \cos(kx)\} \ni k = \frac{\sqrt{2mE}}{\hbar}$$
(15)

$$\cos(kx) \neq 0 \text{ when } x = 0 \Rightarrow A\sin(kx) \text{ is our solution.} \quad \exists k = \frac{\sqrt{2mE}}{\hbar}$$
 (16)

when potential is 0 at
$$x = 0$$
 and L, $k = \frac{n\pi}{L}$, $n = \{1, 2, 3, ...\}$ (17)

therefore:
$$\frac{\sqrt{2mE_n}}{\hbar} = \frac{n\pi}{L} \Rightarrow E_n = \frac{n^2\pi^2\hbar^2}{wmL^2}$$
 (18)

• A is found by normalizing the probability density integral

$$\int_{-\infty}^{\infty} \Psi^* \Psi dx = \int_0^L A^2 \sin^2(\frac{n\pi x}{L}) dx = A^2 \frac{L}{2} \text{ review trig calc and show the process here}$$
 (19)

Set the above to 1 to find A

$$\frac{A^2L}{2} = 1 \Rightarrow A = \sqrt{\frac{2}{L}} \tag{20}$$

Therefore:
$$\psi = \sqrt{\frac{2}{L}} \sin(\frac{n\pi}{L})$$
 for an infinite well (21)

• Parabolic Potential Well (simple harmonic oscillator)

$$V(x) = kx^2, E_n = (n + \frac{1}{2})\hbar\omega \tag{22}$$

• Coulombic Potential Well

$$\frac{d^2}{d\phi^2}\Phi + m^2\Phi = 0 \Rightarrow \Phi_m(\phi) = Ae^{jm\phi}$$
(23)

$$1 = \int_{0}^{2\pi} \Psi^* \Psi d\psi \Rightarrow \int_{0}^{2\pi} \Phi_m^*(\phi) \Phi_m(\phi) d\phi = 1$$
 (24)

$$\Rightarrow A^2 \int_0^{2\pi} e^{-jm\phi} e^{jm\phi} d\phi \tag{25}$$

$$A^2 \int_0^{2\pi} d\phi = 2\pi A^2 \tag{26}$$

$$A = \frac{1}{\sqrt{2\pi}} \Rightarrow \Phi_m(\phi) = \frac{1}{\sqrt{2\pi}} e^{jm\phi}$$

$$\Rightarrow m = \{..., -3, -2, -1, 0, 1, ...\}$$
(27)

similar for $\Theta_l(\theta)$ and $R_n(r)$

• Atomic numbers describing allowable states in a hydrogen atom n = 1, 2, 3, ... l = 0, 1, 2, 3, ..., n = 1

$$\begin{array}{l} l=0,1,2,3,...,n-1 \\ m(m_l)=-l,...,-2,-1,0,1,2,...,l \\ s(m_s)=\frac{\pm \hbar}{2} \end{array}$$

	n	1	m	$\frac{s}{\hbar}$	Allowable states in subshell	Allowable states in complete shell
	1	0	0	$\pm \frac{1}{2}$	2	2
	2	0	0	$\pm \frac{1}{2}$	2	
	2	1	-1	$\pm \frac{1}{2}$		8
	2	1	0	$\pm \frac{1}{2}$	6	
	2	1	1	$\pm \frac{1}{2}$		
	3	0	0	$\pm \frac{1}{2}$	2	18
•	3	1	-1	$\pm \frac{1}{2}$		
	3	1	0	$\pm \frac{1}{2}$	6	18
	3	1	1	$\pm \frac{1}{2}$		
	3	2	-2	$\pm \frac{1}{2}$		
	3	2	-1	$\pm \frac{1}{2}$		
	3	2	0	$\pm \frac{1}{2}$	10	18
	3	2	1	$\pm \frac{1}{2}$		
	3	2	2	$\pm \frac{1}{2}$		

- n is the principle atomic number
- \bullet 1 is the number that determines s,p,d,f,g,...

3 Chapter 3

• Equilibrium number of EHP's in pure Si at room temp:

$$10^{10} \frac{EHP}{cm^3}$$

 $\bullet\,$ Si atom density in pure Si at room temp:

$$5*10^{22}\frac{atoms}{cm^3}$$

• Releationship of (E,k) for a free electron related to electron mass

$$\frac{d^2E}{dk^2} = \frac{\hbar^2}{m} \Rightarrow m^* = \frac{\hbar^2}{\frac{d^2E}{dk^2}} \text{ so the curvature of the band determines the } e^- \text{ effective mass}$$
 (28)

• Velocity of an electron (v) is the group velocity of a quantum mechanical electron wavepacket

$$v = \frac{d\omega}{dk} = (\frac{1}{\hbar})\frac{dE}{dk} \tag{29}$$

• Rate of recombination of electrons and holes r_i is proportional to equilibrium concentrations of electrons and holes n_0 and n_0

$$r_i = \alpha_r n_0 p_0 = \alpha_r n_i^2 = g_i \tag{30}$$

• Calculating the approximate energy required to excite a donor electron into conduction band.

Consider the loosely bound electron as circling the tightly bound "core" electons. Magnitude of the "ground state" is:

$$E = \frac{mq^4}{2k^2\hbar^2} \ni k = 4\pi\epsilon_0\epsilon_r, m \equiv m_n^* \text{ (conductivity effective mass)}$$
 (31)

• Radius of of electron orbit around donor, assuming ground state. Equation was pulled from chapter 2

$$r = \frac{4\pi\epsilon_r\epsilon_0\hbar^2}{m_n^*q^2} \tag{32}$$

• Intrinsic carrier concentration n_i of Si is about $10^{10} cm^{-3}$ at room temperature

3.1 Carrier Concentrations

• Standard Fermi Equation:

$$f(E) = \frac{1}{1 + e^{\frac{(E - E_F)}{kT}}} \ni k \text{ is the Boltzman constant } k = 8.62 * 10^{-5} \frac{eV}{K} = 1.38 * 10^{-23} \frac{J}{K}$$
 (33)

- Calculate the number of electrons and holes in a semiconductor when you know the density of states in valence and conduction bands are known
 - Concentration of electrons in the conduction band by integral:

$$n_0 = \int_{E_c}^{\infty} f(E)N(E)dE \ni N(E)d(E) \text{ is the density of states } (cm^{-3}) \text{ in the energy range of dE}$$
 (34)

- Concentration of electrons in the conduction band by using Effective Density of states:

$$n_0 = N_c f(E_c) \ni N_c$$
 is the effective density of states at E_c (35)

- When E- E_F is several kT we can simplify the equation by recognizing that the exponential dominates the denominator

$$f(E_c) = \frac{1}{1 + e^{\frac{(E - E_F)}{kT}}} \Rightarrow e^{\frac{(E - E_F)}{kT}}$$
 (36)

$$n_0 = N_c e^{-\frac{E_c - E_F}{kT}} (37)$$

- Effective Density of States is:

$$N_c = 2(\frac{2\pi m_n^* kT}{h^2})^{\frac{3}{2}} \ni m_n^* \equiv \text{ the density of states effective mass for electrons}$$
 (38)

- Density of States Effective Mass for Electrons is:

$$(m_n^*)^{\frac{3}{2}} = 6(m_1 m_t^2)^{\frac{1}{2}} \tag{39}$$

- So by similar reasoning, the concentration of holes in the valence band is:

$$p_0 = N_v[1 - f(E_v)] (40)$$

where N_v is the effective density of states for the valence band.

- The probability of finding an empty state at E_v is:

$$1 - f(E_v) = 1 - \frac{1}{1 + e^{\frac{E_V - E_F}{kT}}} \simeq e^{-\frac{(E_F - E_v)}{kT}}$$
(41)

- So the concentration of holes in the valence band is:

$$p_0 = N_v e^{-\frac{E_F - E_v}{kT}} (42)$$

- With effective density of states in the valence band:

$$N_v = 2(\frac{2\pi m_p^* kT}{h^2})^{\frac{3}{2}} \tag{43}$$

- For intrinsic material, E_F is at some intrinsic level E_i near the middle of the band gap. If $N_v = N_c$ then it actually is the middle of the band gap. Usually there is a difference in effective masses, though so there is usually a difference.
- Intrinsic electron and hole concentrations are:

$$n_i = N_c e^{-\frac{E_c - E_i}{kT}}, p_i = N_v e^{-\frac{E_i - E_v}{kT}}$$
(44)

- The product of n_0 and p_0 at equilibrium is a constant for a particular material and temperature, even if the doping is varied

$$n_0 p_0 = (N_c e^{-\frac{E_c - E_i}{kT}}) (N_v e^{-\frac{E_i - E_v}{kT}}) = N_c N_v e^{-\frac{E_c - E_v}{kT}} = N_c N_v e^{-\frac{E_g}{kT}}$$
(45)

$$n_i p_i = (N_c e^{-\frac{E_c - E_i}{kT}}) (N_v e^{-\frac{E_i - E_v}{kT}}) = N_c N_v e^{-\frac{E_g}{kT}}$$
(46)

$$n_i = p_i \Rightarrow \sqrt{N_c N_v} e^{-\frac{E_g}{2kT}}, \quad n_0 p_0 = n_i^2$$

$$\tag{47}$$

$$n_0 = n_i e^{-\frac{E_F - E_i}{kT}}$$

$$p_0 = n_i e^{-\frac{E_i - E_F}{kT}}$$

$$(48)$$

$$p_0 = n_i e^{-\frac{E_i - E_F}{kT}} \tag{49}$$

Temperature Dependence of Carrier Concentrations

The exponential temperature dependence on the intrinsic carrier concentration dominates the other factors:

$$n_i(T) = 2\left(\frac{2\pi kT}{h^2}\right)^{\frac{3}{2}} (m_n^* m_p^*)^{\frac{3}{4}} e^{-\frac{E_g}{2kT}}$$
(50)

3.3 Compensation and Space Charge Neutrality

Compensation changes the effective number of donors:

$$N_{d_e} = N_d - N_a$$
 when the number of donors exceeds the number of acceptors (51)

$$N_{a_e} = N_a - N_d$$
 when the number of acceptors exceeds the number of donors (52)

• Space Charge Neutrality dictates that the number of positive charges (holes and ionized donor atoms) must balance the number of negative charges (electrons and ionized acceptor atoms):

$$p_0 + N_d^+ = n_0 + N_a^- \Rightarrow n_0 = p_0 + (N_d^+ - N_a^-)$$
(53)

For a material that is doped n-type and the material is in the extrinsic region, we can approximate by recognizing that the donors dominate:

$$n_0 \simeq N_d - N_a \tag{54}$$

Drift of Carriers in Electric and Magnetic Fields 4

4.1 Conductivity and Mobility